L6390

High-voltage high/low-side driver

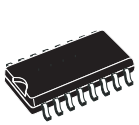
Datasheet – production data

Features

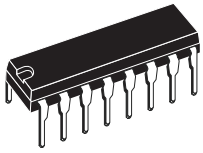
- High-voltage rail up to 600 V
- dV/dt immunity ±50 V/nsec in full temperature range
- Driver current capability:
  - 290 mA source
  - 430 mA sink
- Switching times 75/35 nsec rise/fall with 1 nF load
- 3.3 V, 5 V TTL/CMOS inputs with hysteresis
- Integrated bootstrap diode
- Operational amplifier for advanced current sensing
- Comparator for fault protection
- Smart shutdown function
- Adjustable deadtime
- Interlocking function
- Compact and simplified layout
- Bill of material reduction
- Effective fault protection
- Flexible, easy and fast design

Applications

- Motor driver for home appliances, factory automation, industrial drives
- HID ballasts, power supply units



SO-16



DIP-16

Description

The L6390 is a high-voltage device manufactured with BCD™ “offline” technology. It is a single-chip half bridge gate driver for N-channel Power MOSFETs or IGBT.

The high-side (floating) section is designed to stand a voltage rail up to 600 V. The logic inputs are CMOS/TTL compatible down to 3.3 V for easy microcontroller/DSP interfacing.

The IC embeds an operational amplifier suitable for advanced current sensing in applications such as field oriented motor control.

An integrated comparator is available for protection against overcurrent, overtemperature, etc.

Table 1. Device summary

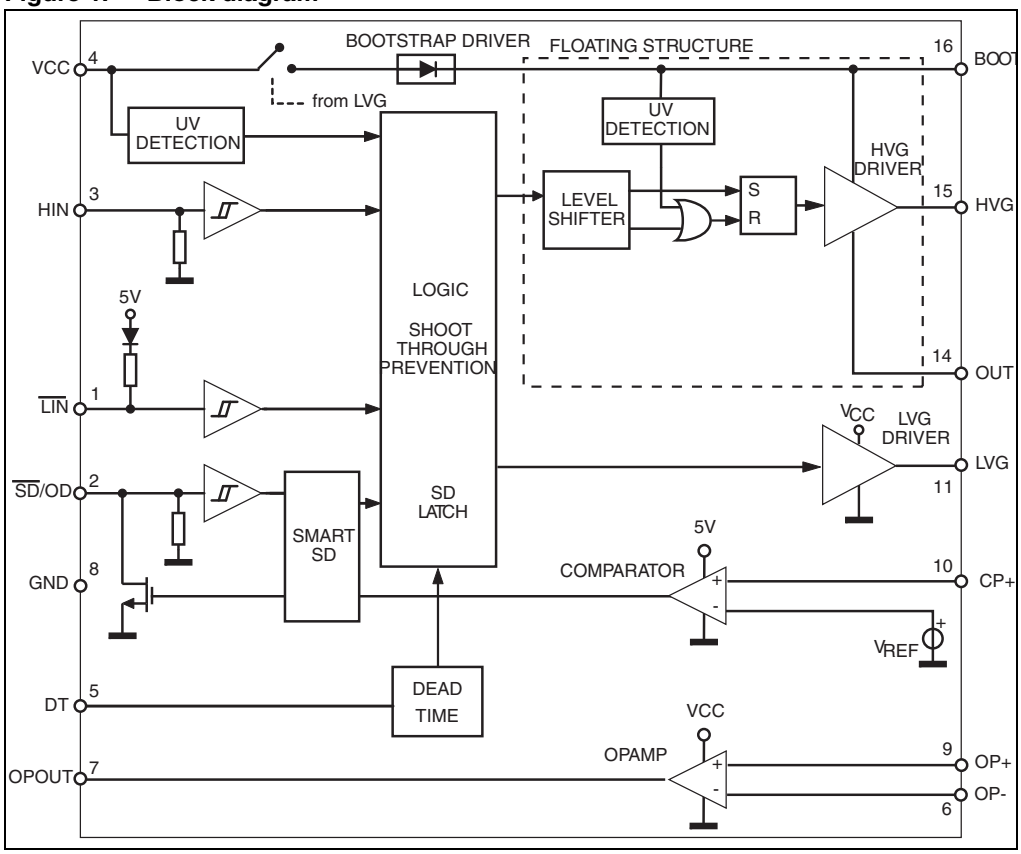
Order code	Package	Packaging
L6390N	DIP-16	Tube
L6390D	SO-16	Tube
L6390DTR	SO-16	Tape and reel

This is information on a product in full production. www.st.com

Contents

1 Block diagram

Figure 1. Block diagram



2 Pin connection

Figure 2. Pin connection (top view)

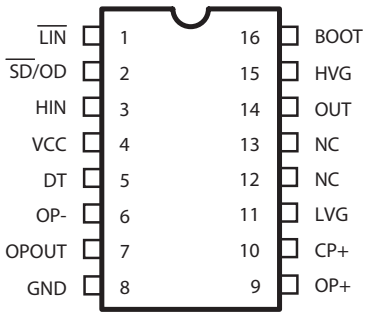


Table 2. Pin description

Pin n #	Pin name	Type	Function
1	$\overline{\text{LIN}}$	I	Low-side driver logic input (active low)
2	$\overline{\text{SD}}$/OD (1)	I/O	Shutdown logic input (active low)/open drain (comparator output)
3	HIN	I	High-side driver logic input (active high)
4	VCC	P	Lower section supply voltage
5	DT	I	Deadtime setting
6	OP-	I	Op amp inverting input
7	OPOUT	O	Op amp output
8	GND	P	Ground
9	OP+	I	Op amp non inverting input
10	CP+	I	Comparator input
11	LVG (1)	O	Low-side driver output
12, 13	NC		Not connected
14	OUT	P	High-side (floating) common voltage
15	HVG (1)	O	High-side driver output
16	BOOT	P	Bootstrap supply voltage

1. The circuit provides less than 1 V on the LVG and HVG pins (@ Isink = 10 mA), with V_{CC} > 3 V. This allows the omission of the “bleeder” resistor connected between the gate and the source of the external MOSFET normally used to hold the pin low; the gate driver assures low impedance also in SD condition.

3 Truth table

Table 3. Truth table

Input			Output	
$\overline{SD}$	$\overline{LIN}$	HIN	LVG	HVG
L	X	X	L	L
H	H	L	L	L
H	L	H	L	L
H	L	L	H	L
H	H	H	L	H

Note: X: don't care.

4 Electrical data

4.1 Absolute maximum ratings

Table 4. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		Min.	Max.	
V_{cc}	Supply voltage	- 0.3	21	V
V_{out}	Output voltage	V_{boot} - 21	V_{boot} + 0.3	V
V_{boot}	Bootstrap voltage	- 0.3	620	V
V_{hvg}	High-side gate output voltage	V_{out} - 0.3	V_{boot} + 0.3	V
V_{lvg}	Low-side gate output voltage	- 0.3	V_{cc} + 0.3	V
V_{op+}	Op amp non-inverting input	- 0.3	V_{cc} + 0.3	V
V_{op-}	Op amp inverting input	- 0.3	V_{cc} + 0.3	V
V_{cp+}	Comparator input voltage	- 0.3	V_{cc} + 0.3	V
V_i	Logic input voltage	- 0.3	15	V
V_{od}	Open drain voltage	- 0.3	15	V
dV_{out}/dt	Allowed output slew rate		50	V/ns
P_{tot}	Total power dissipation (T_A = 25 °C)		800	mW
T_J	Junction temperature		150	°C
T_{stg}	Storage temperature	-50	150	°C

Note: ESD immunity for pins 14, 15 and 16 is guaranteed up to 1 kV (human body model).

4.2 Thermal data

Table 5. Thermal data

Symbol	Parameter	SO-16	DIP-16	Unit
$R_{th(JA)}$	Thermal resistance junction-to-ambient	155	100	°C/W

4.3 Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Pin	Parameter	Test condition	Min.	Max.	Unit
V_{cc}	4	Supply voltage		12.5	20	V
V_{BO} (1)	16-14	Floating supply voltage		12.4	20	V
V_{out}	14	DC output voltage		- 9 (2)	580	V
f_{sw}		Switching frequency	HVG, LVG load C_L = 1 nF		800	kHz
T_J		Junction temperature		-40	125	°C

1. $V_{BO} = V_{boot} - V_{out}$.
2. LVG off. Vcc = 12.5 V. Logic is operational if V_{boot} > 5 V. Refer to AN2738 for more details.

5 Electrical characteristics

5.1 AC operation

Table 7. AC operation electrical characteristics (V_{CC} = 15 V; T_J = +25 °C)

Symbol	Pin	Parameter	Test condition	Min.	Typ.	Max.	Unit
t_{on}	1 vs. 11	High/low-side driver turn-on propagation delay	V_{out} = 0 V V_{boot} = V_{cc} C_L = 1 nF V_i = 0 to 3.3 V See *Figure 3.*	50	125	200	ns
t_{off}	3 vs. 15	High/low-side driver turn-off propagation delay		50	125	200	ns
t_{sd}	2 vs. 11, 15	Shutdown to high/low-side driver propagation delay		50	125	200	ns
t_{isd}		Comparator triggering to high/low-side driver turn-off propagation delay	Measured applying a voltage step from 0 V to 3.3 V to pin CP+.	50	200	250	ns
MT		Delay matching, HS and LS turn-on/off				30	ns
DT	5	Deadtime setting range (1)	R_{DT} = 0, C_L = 1 nF	0.1	0.18	0.25	µs
			R_{DT} = 37 kΩ, C_L = 1 nF, C_{DT} = 100 nF	0.48	0.6	0.72	µs
			R_{DT} = 136 kΩ, C_L = 1 nF, C_{DT} = 100 nF	1.35	1.6	1.85	µs
			R_{DT} = 260 kΩ, C_L = 1 nF, C_{DT} = 100 nF	2.6	3.0	3.4	µs
MDT		Matching deadtime (2)	R_{DT} = 0, C_L = 1 nF			80	ns
			R_{DT} = 37 kΩ, C_L = 1 nF, C_{DT} = 100 nF			120	ns
			R_{DT} = 136 kΩ, C_L = 1 nF, C_{DT} = 100 nF			250	ns
			R_{DT} = 260 kΩ, C_L = 1 nF, C_{DT} = 100 nF			400	ns
t_r	11, 15	Rise time	C_L = 1 nF		75	120	ns
t_f		Fall time	C_L = 1 nF		35	70	ns

1. See *Figure 4 on page 9*.
2. MDT = | DT_{LH} - DT_{HL} | see *Figure 5 on page 13*.

Figure 3. Timing

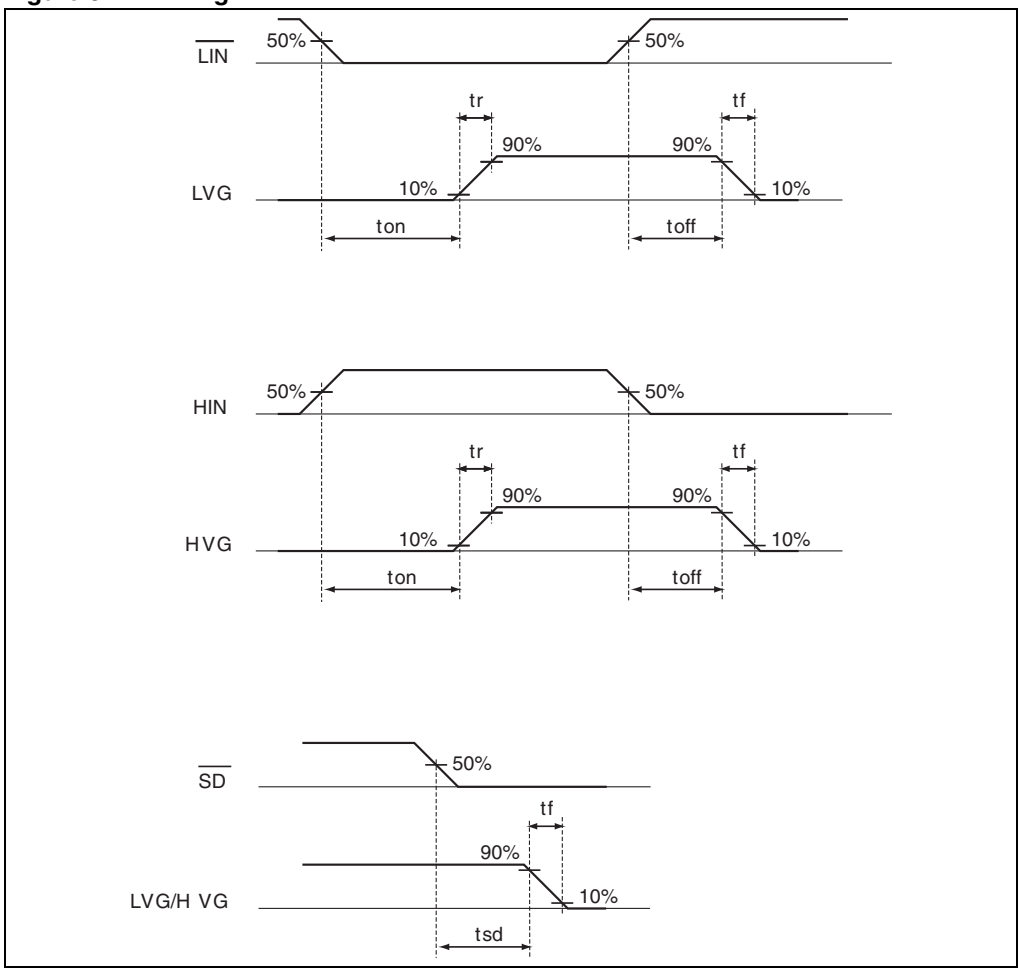
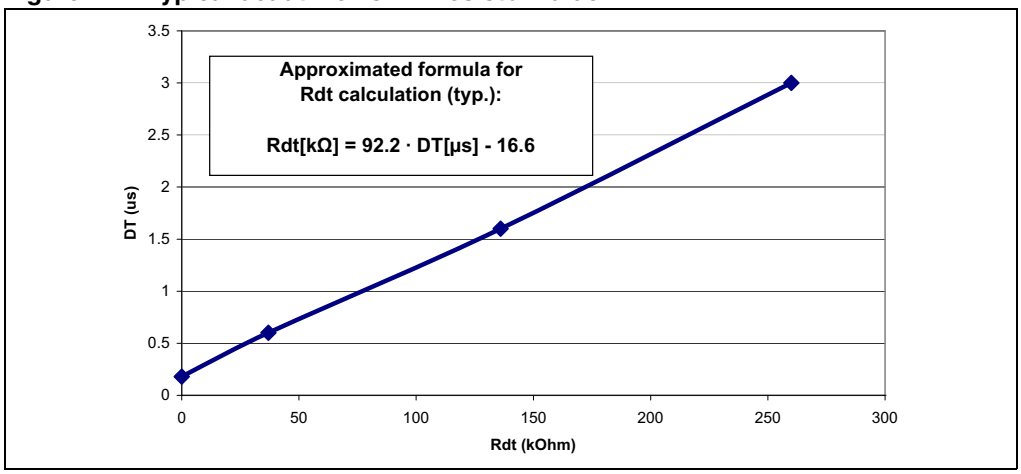


Figure 4. Typical deadtime vs. DT resistor value



5.2 DC operation

Table 8. DC operation electrical characteristics (V_{CC} = 15 V; T_J = + 25 °C)

Symbol	Pin	Parameter	Test condition	Min.	Typ.	Max.	Unit
Low supply voltage section							
V_{cc_hys}	4	V_{cc} UV hysteresis		1200	1500	1800	mV
V_{cc_thON}		V_{cc} UV turn-ON threshold		11.5	12	12.5	V
V_{cc_thOFF}		V_{cc} UV turn-OFF threshold		10	10.5	11	V
I_{qccu}		Undervoltage quiescent supply current	V_{cc} = 10 V $\overline{SD}$ = 5 V; $\overline{LIN}$ = 5 V; HIN = GND; R_{DT} = 0 Ω; CP+=OP+=GND; OP-=5 V	90	120	150	µA
I_{qcc}		Quiescent current	V_{cc} = 15 V $\overline{SD}$ = 5 V; $\overline{LIN}$ = 5 V; HIN = GND; R_{DT} = 0 Ω; CP+=OP+=GND; OP-=5 V	300	720	1000	µA
V_{ref}		Internal reference voltage		500	540	580	mV
Bootstrapped supply voltage section (1)							
V_{BO_hys}	16	V_{BO} UV hysteresis		1200	1500	1800	mV
V_{BO_thON}		V_{BO} UV turn-ON threshold		11.1	11.5	12.1	V
V_{BO_thOFF}		V_{BO} UV turn-OFF threshold		9.8	10	10.6	V
I_{QBOU}		Undervoltage V_{BO} quiescent current	V_{BO} = 9 V $\overline{SD}$ = 5 V; $\overline{LIN}$ and HIN = 5 V; R_{DT} = 0 Ω; CP+=OP+=GND; OP-=5 V	30	70	110	µA
I_{QBO}		V_{BO} quiescent current	V_{BO} = 15 V $\overline{SD}$ = 5 V; $\overline{LIN}$ and HIN = 5 V; R_{DT} = 0 Ω; CP+=OP+=GND; OP-=5 V	30	150	210	µA
I_{LK}		High-voltage leakage current	$V_{hvg} = V_{out} = V_{boot}$ = 600 V			10	µA
$R_{DS(on)}$		Bootstrap driver on-resistance (2)	LVG ON		120		Ω
Driving buffers section							
I_{so}	11, 15	High/low-side source short-circuit current	$V_{IN} = V_{ih}$ (t_p < 10 µs)	200	290		mA
I_{si}		High/low-side sink short-circuit current	$V_{IN} = V_{il}$ (t_p < 10 µs)	250	430		mA

Table 8. DC operation electrical characteristics (V_{CC} = 15 V; T_J = + 25 °C) (continued)

Symbol	Pin	Parameter	Test condition	Min.	Typ.	Max.	Unit
Logic inputs							
V_{il}	1, 2, 3	Low level logic threshold voltage		0.8		1.1	V
V_{ih}		High level logic threshold voltage		1.9		2.25	V
V_{il_S}	1, 3	Single input voltage	$\overline{LIN}$ and HIN connected together and floating			0.8	V
I_{HINh}	3	HIN logic “1” input bias current	HIN = 15 V	110	175	260	µA
I_{HINl}		HIN logic “0” input bias current	HIN = 0 V			1	µA
I_{LINl}	1	$\overline{LIN}$ logic “0” input bias current	$\overline{LIN}$ = 0 V	3	6	20	µA
I_{LINh}		$\overline{LIN}$ logic “1” input bias current	$\overline{LIN}$ = 15 V			1	µA
I_{SDh}	2	$\overline{SD}$ logic “1” input bias current	$\overline{SD}$ = 15 V	10	40	100	µA
I_{SDl}		$\overline{SD}$ logic “0” input bias current	$\overline{SD}$ = 0 V			1	µA

1. $V_{BO} = V_{boot} - V_{out}$.
2. R_{DSON} is tested in the following way: $R_{DSON} = [(V_{CC} - V_{CBOOT1}) - (V_{CC} - V_{CBOOT2})] / [I_1(V_{CC},V_{CBOOT1}) - I_2(V_{CC},V_{CBOOT2})]$ where I_1 is pin 16 current when $V_{CBOOT} = V_{CBOOT1}$, I_2 when $V_{CBOOT} = V_{CBOOT2}$.

Table 9. Op amp characteristics (1) (V_{CC} = 15 V, T_J = +25 °C)

Symbol	Pin	Parameter	Test condition	Min.	Typ.	Max.	Unit
V_{io}	6, 9	Input offset voltage	V_{ic} = 0 V, V_o = 7.5 V			6	mV
I_{io}		Input offset current	V_{ic} = 0 V, V_o = 7.5 V		4	40	nA
I_{ib}		Input bias current (2)			100	200	nA
V_{icm}		Input common mode voltage range		0		V_{CC}-4	V
V_{OPOUT}	7	Output voltage swing	OPOUT = OP-; no load	0.07		V_{CC}-4	V
I_o		Output short-circuit current	Source, V_{id} = +1; V_o = 0 V	16	30		mA
			Sink,V_{id} = -1; V_o = V_{CC}	50	80		mA
SR		Slew rate	V_i = 1 ÷ 4 V; C_L = 100 pF; unity gain	2.5	3.8		V/µs
GBWP		Gain bandwidth product	V_o = 7.5 V	8	12		MHz
A_{vd}		Large signal voltage gain	R_L = 2 kΩ	70	85		dB
SVR		Supply voltage rejection ratio	vs. V_{CC}	60	75		dB
CMRR		Common mode rejection ratio		55	70		dB

1. Operational amplifier is disabled when V_{CC} is in UVLO condition.
2. The direction of input current is out of the IC.

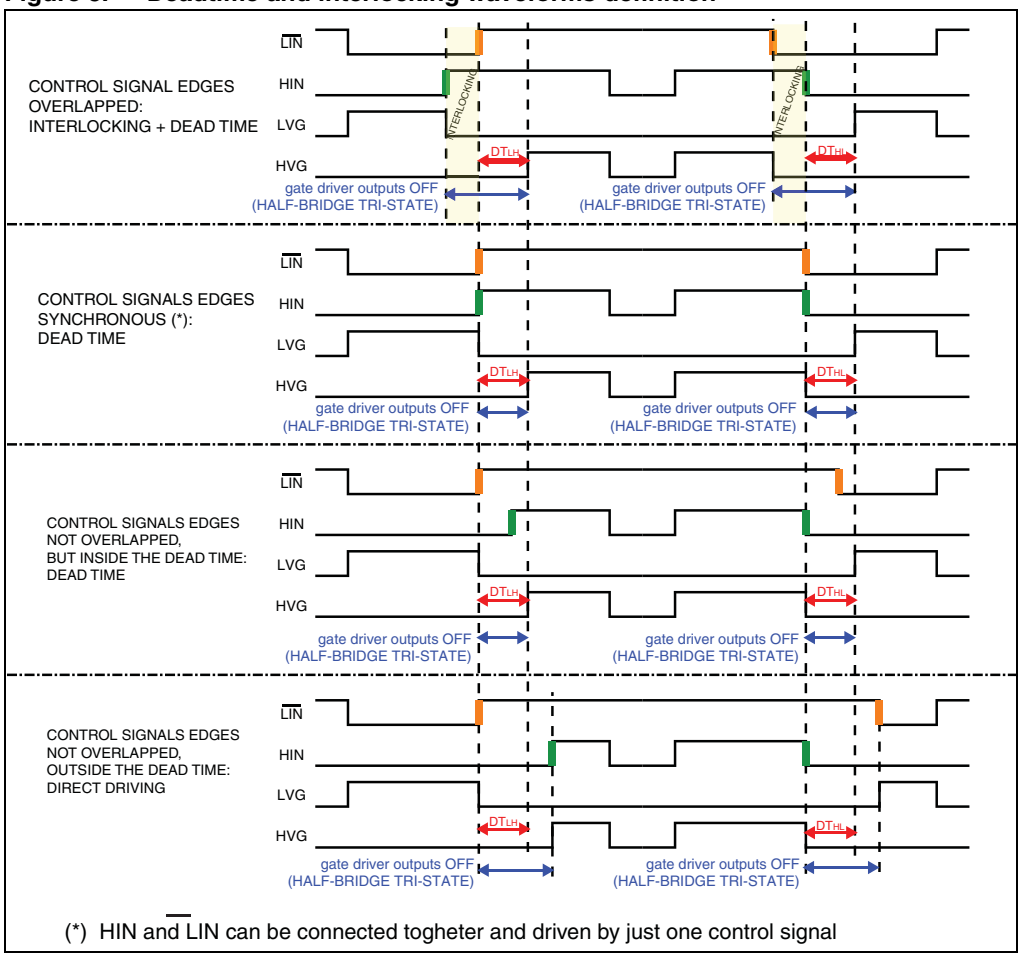
Table 10. Sense comparator characteristics (1) (V_{CC} = 15 V, T_J = +25 °C)

Symbol	Pin	Parameter	Test condition	Min.	Typ.	Max.	Unit
I_{ib}	10	Input bias current	V_{CP+} = 1 V			1	µA
V_{ol}	2	Open drain low-level output voltage	I_{od} = - 3 mA			0.5	V
t_{d_comp}		Comparator delay	$\overline{SD}$/OD pulled to 5 V through 100 kΩ resistor		90	130	ns
SR	2	Slew rate	C_L = 180 pF; R_{pu} = 5 kΩ		60		V/µs

1. Comparator is disabled when V_{CC} is in UVLO condition.

6 Waveforms definition

Figure 5. Deadtime and interlocking waveforms definition

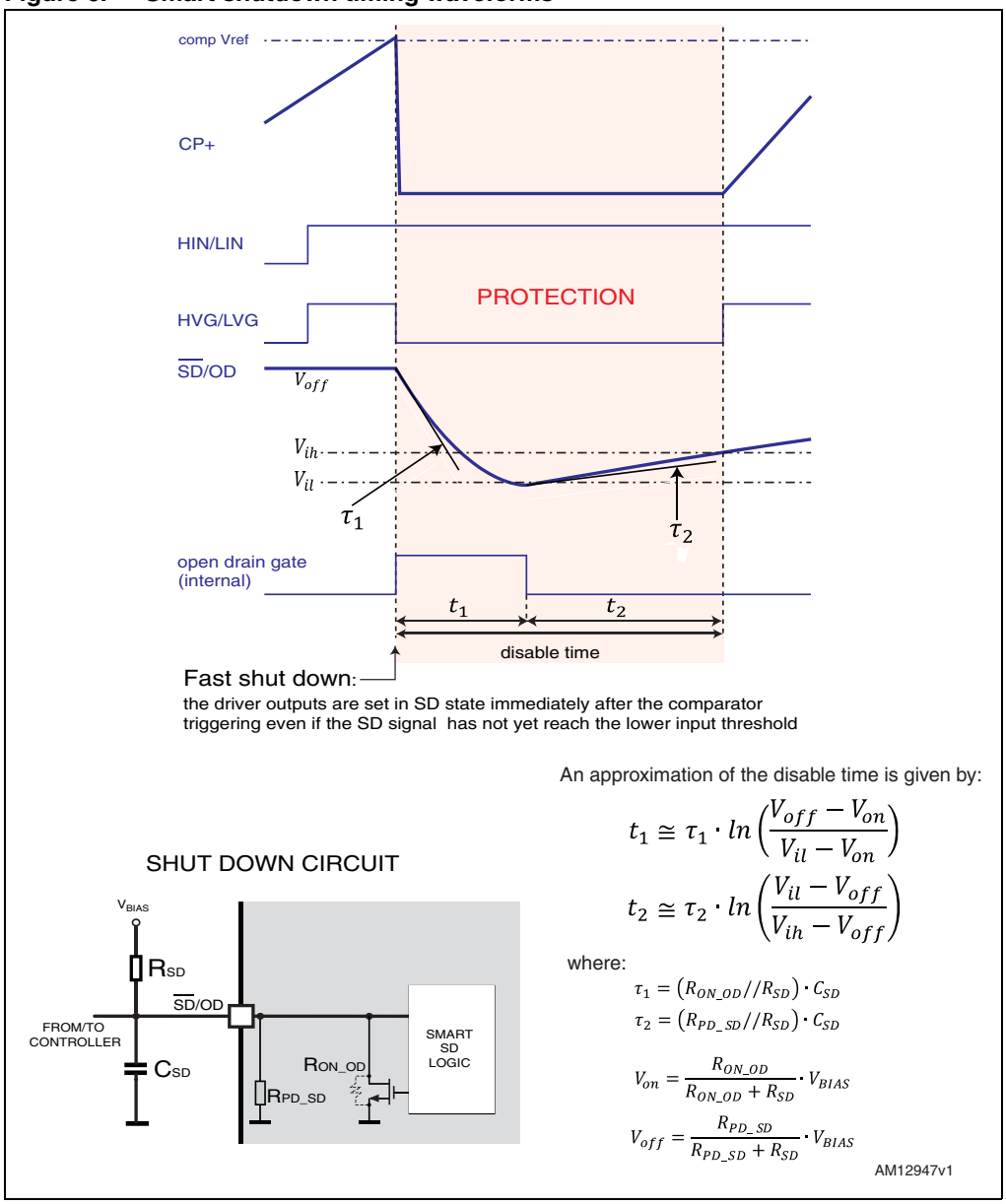


(*) HIN and $\overline{\text{LIN}}$ can be connected togheter and driven by just one control signal

7 Smart shutdown function

The L6390 integrates a comparator committed to the fault sensing function. The comparator has an internal voltage reference V_{ref} connected to the inverting input, while the non-inverting input is available on pin 10. The comparator input can be connected to an external shunt resistor in order to implement a simple overcurrent detection function. The output signal of the comparator is fed to an integrated MOSFET with the open drain output available on pin 2, shared with the SD input. When the comparator triggers, the device is set in shutdown state and both its outputs are set to low level leaving the half-bridge in tri-state.

Figure 6. Smart shutdown timing waveforms

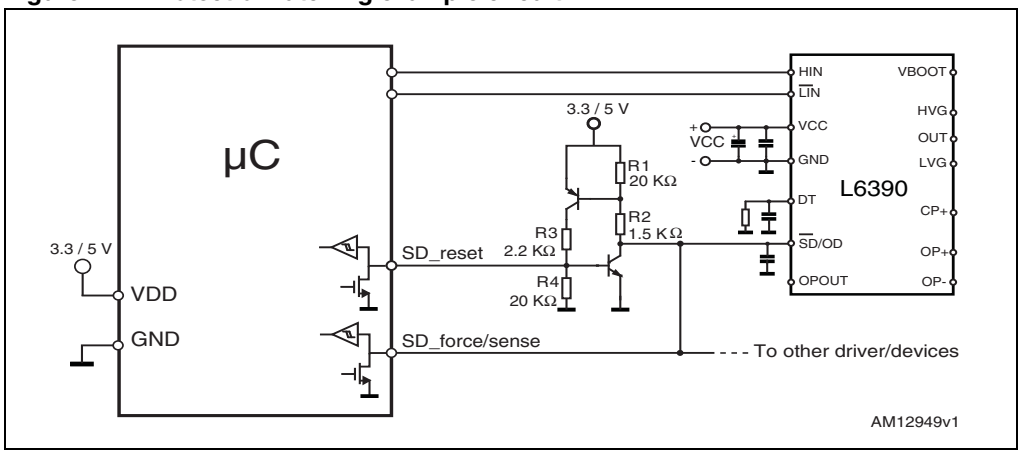


In common overcurrent protection architectures the comparator output is usually connected to the SD input and an RC network is connected to this SD/OD line in order to provide a mono-stable circuit, which implements a protection time that follows the fault condition. Differently from the common fault detection systems, the L6390 smart shutdown architecture allows immediate turn-off of the outputs of the gate driver in the case of fault, by minimizing the propagation delay between the fault detection event and the actual output switch-off. In fact, the time delay between the fault detection and the output turn-off is no longer dependent on the value of the external RC network connected to the SD/OD pin. In the smart shutdown circuitry the fault signal has a preferential path which directly switches off the outputs after the comparator triggering. At the same time the internal logic turns on the open drain output and holds it on until the SD voltage goes below the SD logic input lower threshold. When such threshold is reached, the open drain output is turned off, allowing the external pull-up to recharge the capacitor. The driver outputs restart following the input pins as soon as the voltage at the SD/OD pin reaches the higher threshold of the SD logic input. The smart shutdown system provides the possibility to increase the time constant of the external RC network (that determines the disable time after the fault event) up to very large values without increasing the delay time of the protection.

Any external signal provided to the SD pin is not latched and can be used as control signal in order to perform, for instance, PWM chopping through this pin. In fact when a PWM signal is applied to the SD input and the logic inputs of the gate driver are stable, the outputs switch from the low level to the state defined by the logic inputs and vice versa.

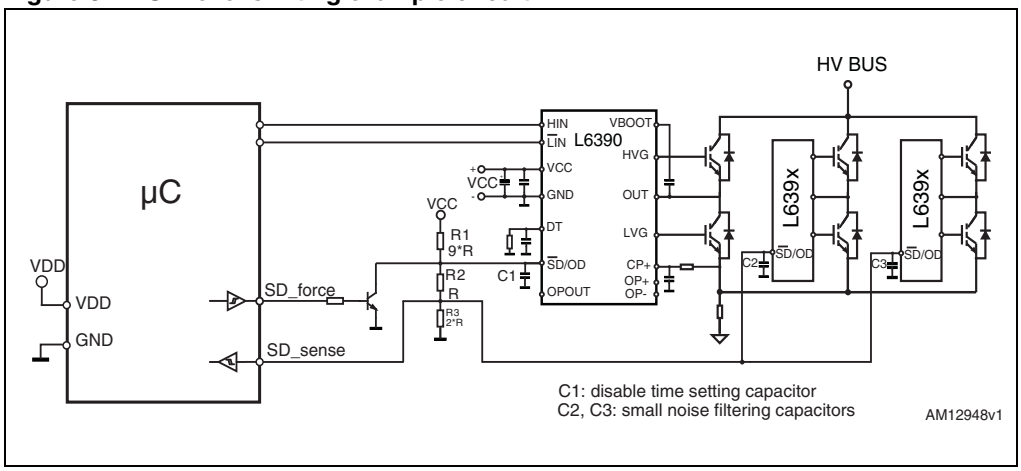
In some applications it may be useful to latch the driver in the shutdown condition for an arbitrary time, until the controller decides to reset it to normal operation. This may, for example, be achieved with a circuit similar to the one shown in *Figure 7*. When the open drain starts pulling down the SD/OD pin, the external latch turns on and keeps the pin to GND, preventing it from being pulled up again once the SD logic input lower threshold is reached and the internal open drain turns off. One pin of the controller is used to release the external latch, and one to externally force a shutdown condition and also to read the status of the SD/OD pin.

Figure 7. Protection latching example circuit



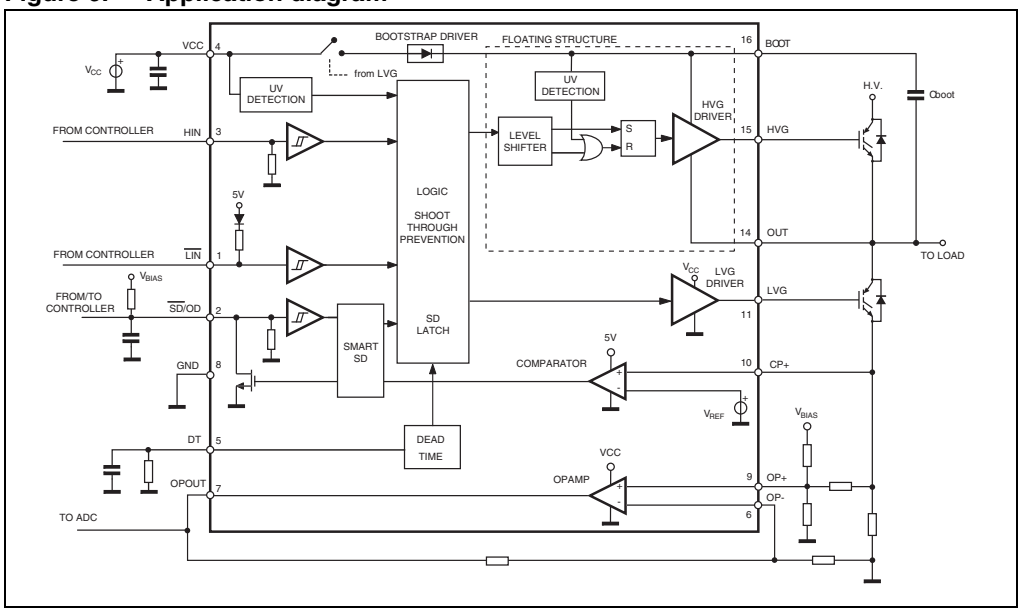
In applications using only one L6390 for the protection of several different legs (such as a single-shunt inverter, for example) it may be useful to implement the resistor divider shown in *Figure 8*. This simple network allows the pushing of the SD pins of the other devices to a voltage lower than L6390 V_{il}, so that each device can reach its low logic level regardless of part-to-part variations of the thresholds.

Figure 8. SD level shifting example circuit



8 Typical application diagram

Figure 9. Application diagram



9 Bootstrap driver

A bootstrap circuitry is needed to supply the high-voltage section. This function is normally accomplished by a high-voltage fast recovery diode (*Figure 10*.a). In the L6390 a patented integrated structure replaces the external diode. It is realized by a high-voltage DMOS, driven synchronously with the low-side driver (LVG), with diode in series, as shown in *Figure 10*.b. An internal charge pump (*Figure 10*.b) provides the DMOS driving voltage.

9.1 C_{BOOT} selection and charging

To choose the proper C_{BOOT} value the external MOS can be seen as an equivalent capacitor. This capacitor C_{EXT} is related to the MOS total gate charge:

Equation 1

$$C_{EXT} = \frac{Q_{gate}}{V_{gate}}$$

The ratio between the capacitors C_{EXT} and C_{BOOT} is proportional to the cyclical voltage loss. It must be:

Equation 2

$$C_{BOOT} >>> C_{EXT}$$

E.g.: if Q_{gate} is 30 nC and V_{gate} is 10 V, C_{EXT} is 3 nF. With C_{BOOT} = 100 nF the drop would be 300 mV.

If HVG must be supplied for a long time, the C_{BOOT} selection must also take the leakage and quiescent losses into account.

E.g.: HVG steady-state consumption is lower than 150 µA, so if HVG T_{ON} is 5 ms, C_{BOOT} must supply 0.75 µC to C_{EXT}. This charge on a 1 µF capacitor means a voltage drop of 0.75 V.

The internal bootstrap driver offers important advantages: the external fast recovery diode can be avoided (it usually has a high leakage current).

This structure can work only if V_{OUT} is close to GND (or lower) and, at the same time, the LVG is on. The charging time (T_{charge}) of the C_{BOOT} is the time in which both conditions are fulfilled and it must be long enough to charge the capacitor.

The bootstrap driver introduces a voltage drop due to the DMOS R_{DSon} (typical value: 120 Ω). This drop can be neglected at low switching frequency, but it should be taken into account when operating at high switching frequency.

The following equation is useful to compute the drop on the bootstrap DMOS:

Equation 3

$$V_{drop} = I_{charge} R_{dson} \rightarrow V_{drop} = \frac{Q_{gate}}{T_{charge}} R_{dson}$$

where Q_{gate} is the gate charge of the external Power MOSFET, R_{dson} is the on-resistance of the bootstrap DMOS and T_{charge} is the charging time of the bootstrap capacitor.

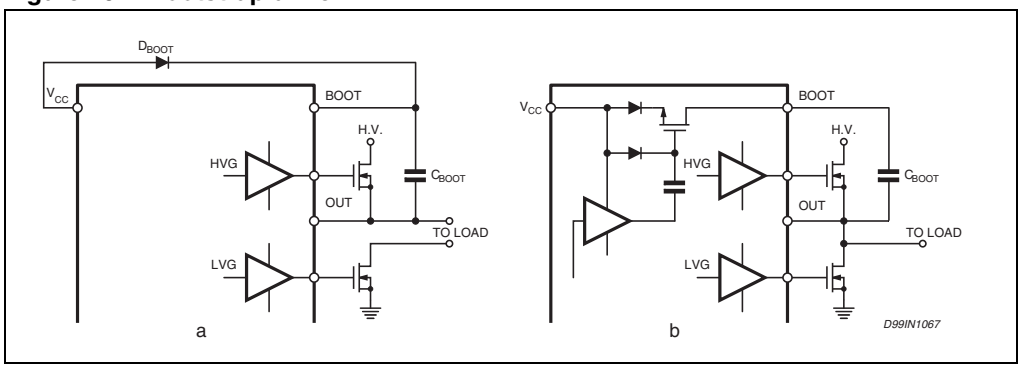
For example: using a Power MOSFET with a total gate charge of 30 nC, the drop on the bootstrap DMOS is about 1 V, if the T_{charge} is 5 µs. In fact:

Equation 4

$$V_{drop} = \frac{30nC}{5\mu s} \cdot 120\Omega \sim 0.7V$$

V_{drop} should be taken into account when the voltage drop on C_{BOOT} is calculated: if this drop is too high, or the circuit topology doesn't allow a sufficient charging time, an external diode can be used.

Figure 10. Bootstrap driver



10 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 11. DIP-16 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
a1	0.51		
B	0.77		1.65
b		0.5	
b1		0.25	
D			20
E		8.5	
e		2.54	
e3		17.78	
F			7.1
I			5.1
L		3.3	
Z			1.27

Figure 11. DIP-16 package dimensions

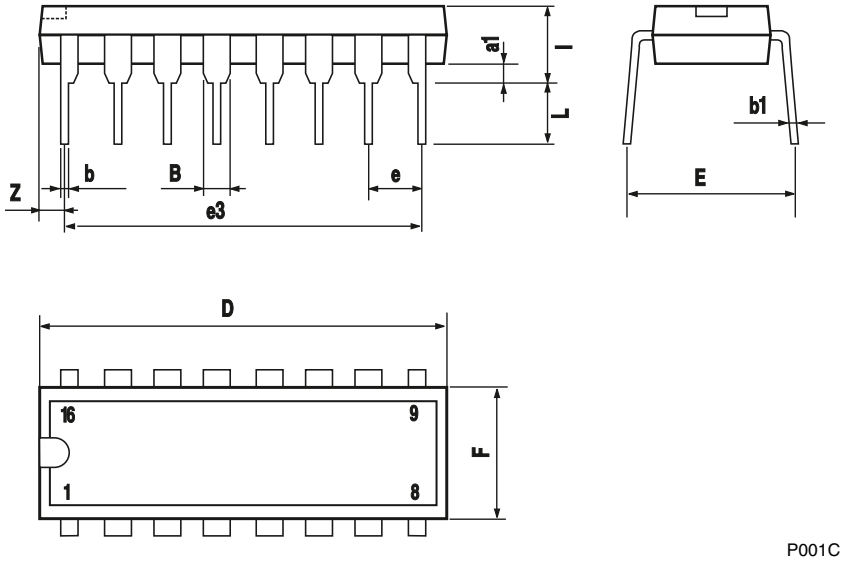


Table 12. SO-16 narrow mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		
b	0.31		0.51
c	0.17		0.25
D	9.80	9.90	10.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50
L	0.40		1.27
k	0		8°
ccc			0.10

Figure 12. SO-16 narrow package dimensions

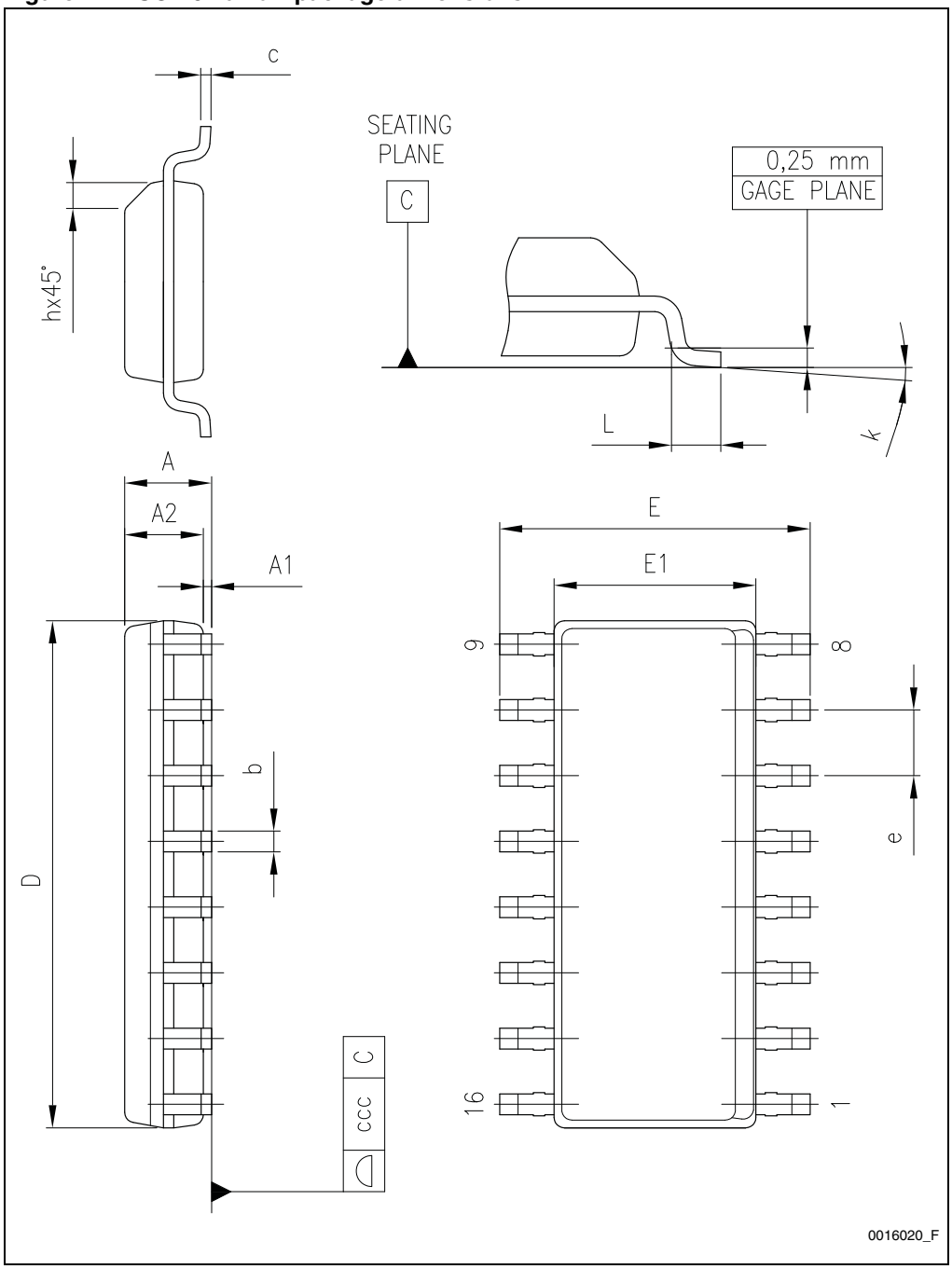
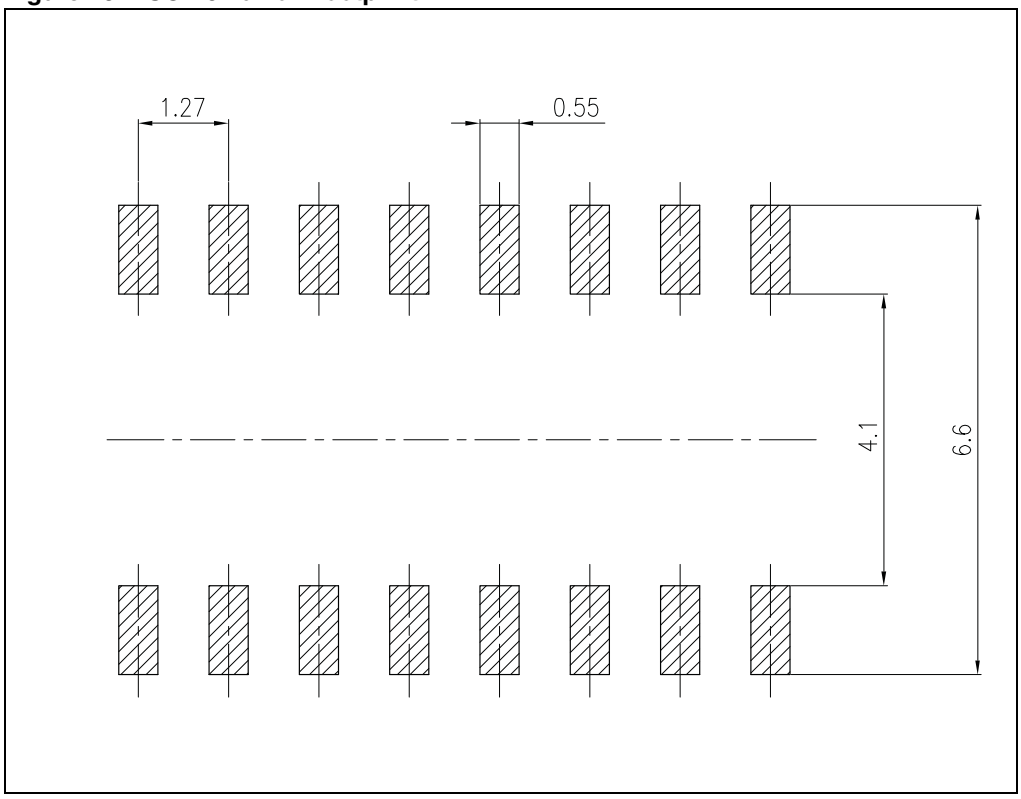


Figure 13. SO-16 narrow footprint



11 Revision history

Table 13. Document revision history

Date	Revision	Changes
29-Feb-2008	1	First release
09-Jul-2008	2	Updated: Cover page, *Table 2 on page 4*, *Table 3 on page 5*, *Section 4 on page 6*, *Section 5 on page 8*, *Section 9.1 on page 18*
17-Sep-2008	3	Updated test condition values on *Table 8* and *Table 9*
17-Feb-2009	4	Updated *Table 7 on page 8*, *Table 8 on page 10*, *Table 9 on page 12* Added *Table 4 on page 6*
11-Aug-2010	5	Updated *Table 1 on page 1*, *Table 7 on page 8*, *Table 9 on page 12*, *Table 10 on page 12*
10-Jul-2012	6	*Table 7* changed test conditions of DT and MDT values. *Table 8* added minimum values to I_{qccu}-I_{qcc}-I_{QBOU}- $I_{QBO.}$ *Table 8* changed V_{BO_thON} and V_{BO_thOFF} minimum and maximum values. *Table 9* and *Table 10* added footnote to the title of the tables. Changed HVG values on page 17. Updated SO-16 narrow mechanical data. Changed *Section 7* and added *Figure 7* and *Figure 8*.
25-Jul-2012	7	Content reworked in *Section 9: Bootstrap driver* to improve readability, no technical changes.